

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
14 September 2023 (14.09.2023)



(10) International Publication Number
WO 2023/172207 A2

(51) International Patent Classification:
Not classified

(21) International Application Number:
PCT/SG2023/050160

(22) International Filing Date:
13 March 2023 (13.03.2023)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10202202509U 11 March 2022 (11.03.2022) SG

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS,

RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— of inventorship (Rule 4.17(iv))

Published:

— without international search report and to be republished upon receipt of that report (Rule 48.2(g))

(54) Title: MULTI-LAYER CONTACT STRUCTURE, PHOTOVOLTAIC CELL AND METHOD OF FABRICATION OF MULTI-LAYER CONTACT STRUCTURE

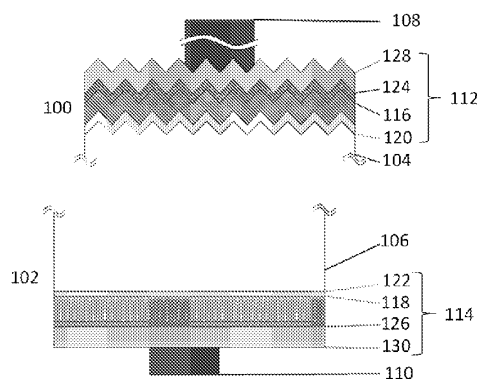


Figure 1

(57) Abstract: Disclosed is a multi-layer contact structure comprising a semiconductor substrate, a terminal electrode, and a contact layer structure. The contact layer structure comprises a metal-containing carrier selective (MCS) layer, the contact layer structure being in intimate contact with the semiconductor substrate and the terminal electrode.

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